Correction to: Strain states and relaxation for α -(Al_xGa_{1-x})₂O₃ thin films on prismatic planes of α -Al₂O₃ in the full composition range: Fundamental difference of a- and m-epitaxial planes in the manifestation of shear strain and lattice tilt

Max Kneiß^{1,a)} , Daniel Splith¹ , Holger von Wenckstern¹ , Michael Lorenz¹ ,
Thorsten Schultz^{2,3} , Norbert Koch^{2,3} , Marius Grundmann¹

¹ Universität Leipzig, Felix Bloch Institute for Solid State Physics, Semiconductor Physics Group, Linnéstraße 5, Leipzig 04103, Germany

² Humboldt Universität zu Berlin, Institut für Physik, Brook-Taylor-Straße 6, Berlin 12489, Germany

³ Helmholtz-Zentrum für Energie und Materialien GmbH, Hahn-Meitner-Platz 1, Berlin 14109, Germany

^{a)} Address all correspondence to this author. e-mail: max.kneiss@physik.uni-leipzig.de

Published online: 19 October 2021

Correction to:

Journal of Materials Research

<https://doi.org/10.1557/s43578-021-00375-3>

This article was updated to correct errors introduced into the reference section during the production process after the author had reviewed the proof.

The original article can be found online at <https://doi.org/10.1557/s43578-021-00375-3>.